

Silicon NPN Power Transistors

2SD1711

DESCRIPTION

- With TO-3PML package
- High voltage;high speed
- High reliability.
- Built-in damper diode

APPLICATIONS

- Ultrahigh-definition CRT display
- Horizontal deflection output applications

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Base |
| 2 | Collector |
| 3 | Emitter |

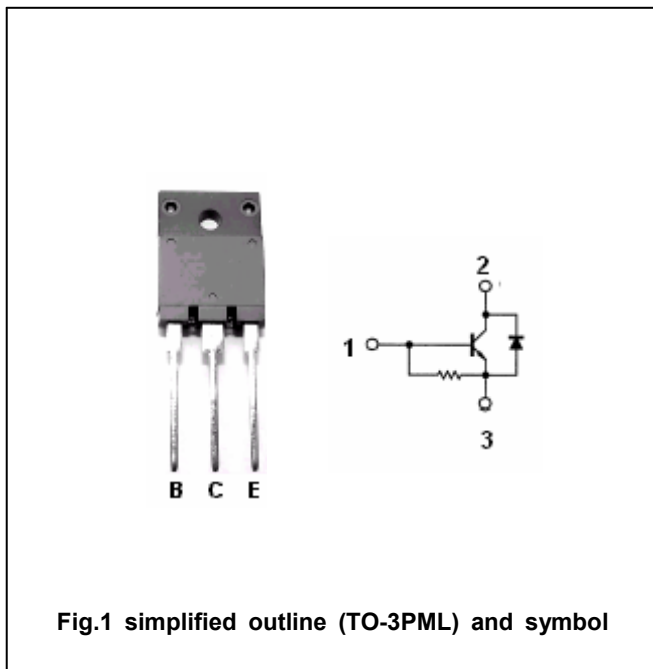


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 1500 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 800 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 5 | V |
| I _C | Collector current | | 5 | A |
| P _C | Collector power dissipation | T _C =25°C | 100 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{CEO(SUS)} | Collector-emitter sustaining voltage | I _C =100mA; I _B =0 | 800 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =4A; I _B =0.8 A | | | 5.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =4A; I _B =0.8 A | | | 1.5 | V |
| I _{EBO} | Emitter cut-off current | V _{EB} =4V; I _C =0 | 40 | | 130 | mA |
| I _{CBO} | Collector cut-off current | V _{CB} =800V; I _E =0 | | | 10 | μA |
| I _{CES} | Collector cut-off current | V _{CE} =1500V; R _{BE} =0 | | | 1 | mA |
| h _{FE} | DC current gain | I _C =0.5 A ; V _{CE} =5V | 10 | | 40 | |

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PACKAGE OUTLINE

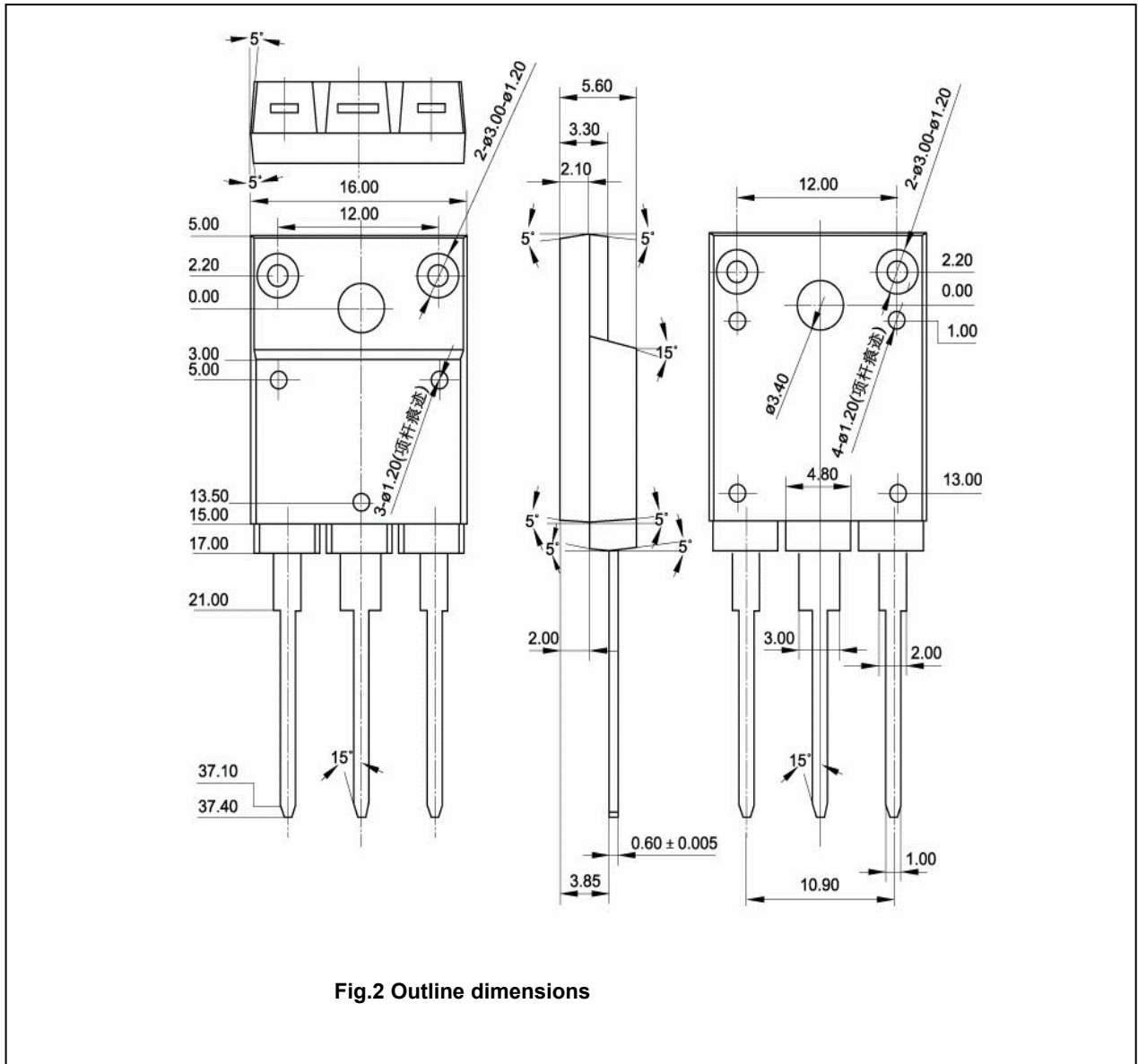


Fig.2 Outline dimensions